

The RM3002 is an NPN silicon planar photo sensitive Darlington Compound Amplifier. This device combines a lens window with an integral light sensing amplifier. The result is extreme sensitivity in a very small package. The planar construction and the stringent process controls prevalent at Raytheon insures the ultimate in reliability.

MECHANICAL DATA

CASE:

JEDEC TO-18

CONNECTION DIAGRAM:

TERMINAL CONNECTIONS:

Lead | Emitter

Lead 2 Base

Lead 3 Collector (Electrically connected to case)

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ELECTRICAL DATA

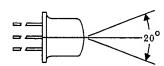
MAXIMUM RATINGS:

Collector to Base Voltage V _{CBO}	lts
Collector to Emitter Voltage (R _{BE} ≤10Ω) V _{CER}	
Collector to Emitter Voltage V _{CEO}	
Emitter to Base Voltage V _{EBO}	lts
Total Device Dissipation @ Case Temperature 25° C	itts itt itt

ELECTRICAL CHARACTERISTICS: @25°C (unless otherwise noted)

PARAMETER	SYM.	CONDITIONS	MIN.	MAX.	UNITS
Dark Current	ICEO	$V_{CE}^{=20} V$		10	mμA
Dark Current	ICEO	V _{CE} =20 V T=150° C		100	μΑ
Collector Dark Current	I _{CBO}	V _{CB} =30 V		10	$m \mu A$
Collector Dark Current	I _{CBO}	V _{CB} =30 V T=150° C		15	μΑ
Light Current Sensitivity		V _{CE} =12 100 foot candle illumination level	25	μA/ft.	Candle

ALIGNMENT:



Maximum sensitivity falls within a 20° cone whose axis coincides with the central axis of the lens.

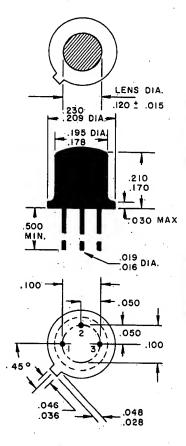
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PHOTO SENSITIVE DARLINGTON COMPOUNI AMPLIFIER

NPN PLANAR

FEATURES

- High Sensitivity
- 3 Lead Configuration
- High Stability
- Low Noise
- High Gain



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RAYTHEON COMPANY

SEMICONDUCTOR DIVISION

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